AMENDMENTS TO THE CLAIMS:

The following listing of claims replaces all prior listings, and all prior versions, of claims in the above-identified application.

LISTING OF CLAIMS:

1. (Currently amended) A circuit connecting material,

wherein the circuit connecting material has ~~having~~ a property that the material can electrically connect a first circuit member in which first circuit electrodes are located on the main surface of a first circuit board, and a second circuit member in which second circuit electrodes are located on the main surface of a second circuit board, when~~wherein~~ insulating layers of silicon dioxide or silicon nitride are located adjacent to at least one of said first circuit electrodes and said second circuit electrodes, with at least some of said insulating layers being formed such that these layers are thicker than said circuit electrodes on the basis of said main surface in at least one of said first and second circuit members;~~,~~

wherein said material contains a bonding agent composition and conductive particles which have a mean particle size of 1 μm or greater but less than 10 μm, and a hardness of 4.4413 to 6.865 GPa; and

wherein said material exhibits, when subjected to a curing treatment, a storage elastic modulus of 0.5 to 3 GPa at 40°C, and a mean coefficient of thermal expansion of 30 to 200 ppm/°C at from 25°C to 100°C.

2. (Original) The circuit connecting material according to claim 1, wherein said conductive particles comprise a core body made of an organic polymer, and a metal layer made of copper, nickel, a nickel alloy, silver or a silver alloy which is

formed on the surface of said core body, and the thickness of said metal layer is 50 to 170 nm.

3. (Previously presented) The circuit connecting material according to claim 1, wherein said conductive particles comprise an outermost layer made of gold or palladium, and the thickness of said outermost layer is 15 to 70 nm.

4. (Previously presented) The circuit connecting material according to claim 1, wherein said bonding agent composition contains an epoxy resin and a latent curing agent for said epoxy resin.

5. (Previously presented) The circuit connecting material according to claim 1, wherein said bonding agent composition contains a radical-polymerizable substance, and a curing agent which generates free radicals when heated.

6. (Previously presented) The circuit connecting material according to claim 1, wherein the glass transition temperature is 60 to 200°C as a result of the curing treatment.

7. (Previously presented) The circuit connecting material according to claim 1, wherein the material further contains a film forming material.

8. (Original) The circuit connecting material according to claim 7, wherein said film forming material is a phenoxy resin.

9. (Previously presented) A film-form circuit connecting material which is formed by forming the circuit connecting material according to claim 1 into shape of a film.

10.-18. (Cancelled).

19. (Currently amended) A method for manufacturing a circuit member connecting structure which comprises a first circuit member in which first circuit electrodes are located on the main surface of a first circuit board, a second circuit member in which second circuit electrodes are located on the main surface of a second circuit board, and a circuit connecting member which is disposed between the main surface of said first circuit member and the main surface of said second circuit member for connecting said first and second circuit members to each other, wherein insulating layers of silicon dioxide or silicon nitride are located adjacent to both~~at least one~~ of said first circuit electrodes and said second circuit electrodes, at least some of said insulating layers being formed so that these layers are thicker than said circuit electrodes on the basis of the main surface of the circuit board in both~~at least one~~ of said first and second circuit members,

said method comprising the steps of:

interposing the film-form circuit connecting material according to claim 9 between the main surface of said first circuit board and the main surface of said second circuit board, and

curing said circuit connecting material by the application of heat and pressure via said first and second circuit members for thereby connecting said first circuit

member and said second circuit member, so that said first circuit electrodes and said second circuit electrodes are electrically connected via said conductive particles.

20. and 21. (Cancelled).

22. (Previously presented) The method for manufacturing a circuit member connecting structure according to claim 19, wherein a difference in thickness between the insulating layer adjacent the first circuit electrodes and the first circuit electrodes is 50 to 600 nm, and a difference in thickness between the insulating layer adjacent the second circuit electrodes and the second circuit electrodes is 50 to 600 nm.

23. (Previously presented) The method for manufacturing a circuit member connecting structure according to claim 19, wherein said film-form circuit connecting material interposed between the main surfaces of the first and second circuit boards has a thickness of 10 to 50 μm.

24. (Previously presented) The circuit connecting material according to claim 6, wherein said glass transition temperature is 60 to 180°C as a result of the curing treatment.

25. (Previously presented) The circuit connecting material according to claim 1, wherein said storage elastic modulus is 0.7 to 2 GPa.

26. (New) The circuit connecting material according to claim 1, wherein said circuit connecting material has said property when said insulating layers are located adjacent to both of said first and second circuit electrodes, with at least some of said insulating layers being formed such that these layers are thicker than said first and second circuit electrodes on the basis of said main surface in both of said first and second circuit members.